

74HC4852-Q100; 74HCT4852-Q100

Dual 4-channel analog multiplexer/demultiplexer with injection-current effect control

Rev. 1 — 12 July 2012

Product data sheet

1. General description

The 74HC4852-Q100; 74HCT4852-Q100 are high-speed Si-gate CMOS devices and are specified in compliance with JEDEC standard no. 7A.

The 74HC4852-Q100; 74HCT4852-Q100 are dual 4-channel analog multiplexers/demultiplexers with common select inputs (S0 and S1). Both multiplexers have a common active LOW enable input (\bar{E}), four independent inputs/outputs (nY0 to nY3) and two common inputs/outputs (1Z, 2Z). The devices feature injection-current effect control, which has excellent value in automotive applications where voltages in excess of the supply voltage are common.

With \bar{E} LOW, two of the eight switches are selected (low impedance ON-state) by S0 and S1. With \bar{E} HIGH, all switches are in the high-impedance OFF-state, independent of S0 and S1.

The injection-current effect control allows signals at disabled analog input channels to exceed the supply voltage without affecting the signal of the enabled analog channel. This eliminates the need for external diode/resistor networks typically used to keep the analog channel signals within the supply-voltage range.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Injection-current cross coupling $< 1\text{ mV/mA}$
- Wide supply voltage range from 2.0 V to 6.0 V for 74HC4852-Q100
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V (C = 200 pf, R = 0 Ω)
- Latch-up performance exceeds 100 mA per JESD 78 Class II level A
- Low ON-state resistance:
 - ◆ 400 Ω (typical) at $V_{CC} = 2.0\text{ V}$
 - ◆ 215 Ω (typical) at $V_{CC} = 3.0\text{ V}$
 - ◆ 120 Ω (typical) at $V_{CC} = 3.3\text{ V}$
 - ◆ 76 Ω (typical) at $V_{CC} = 4.5\text{ V}$
 - ◆ 59 Ω (typical) at $V_{CC} = 6.0\text{ V}$



3. Applications

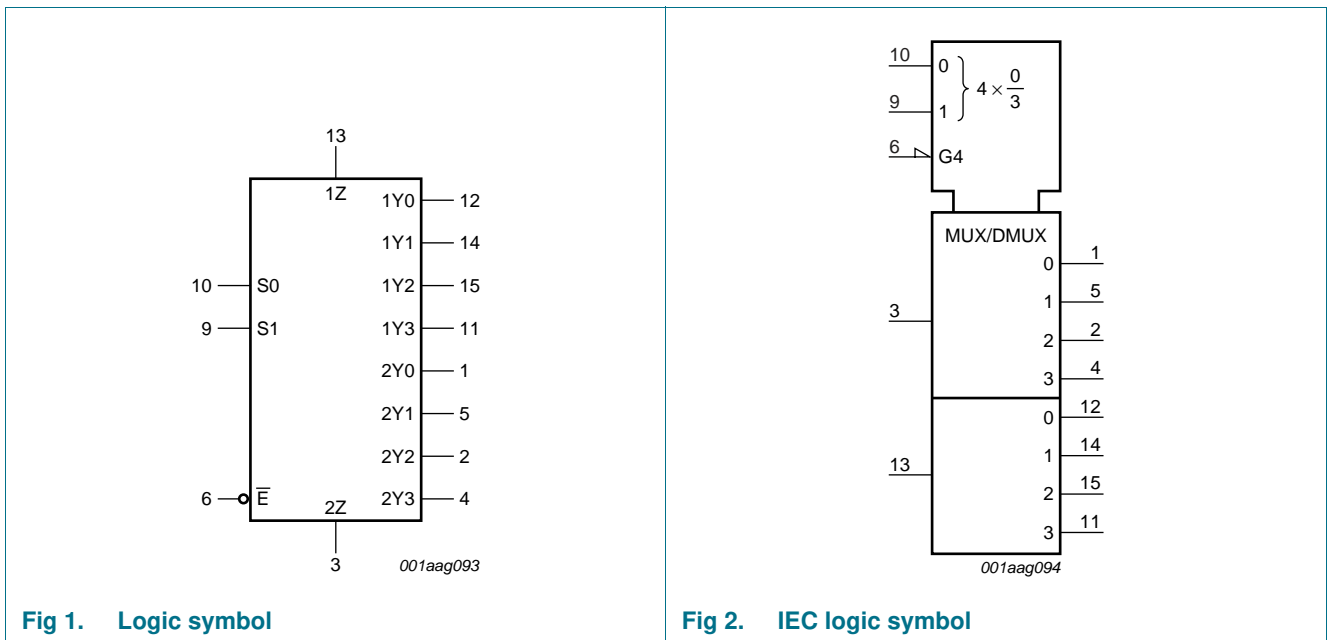
- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating
- Automotive application

4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC4852D-Q100 74HCT4852D-Q100	-40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC4852PW-Q100 74HCT4852PW-Q100	-40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HC4852BQ-Q100 74HCT4852BQ-Q100	-40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

5. Functional diagram



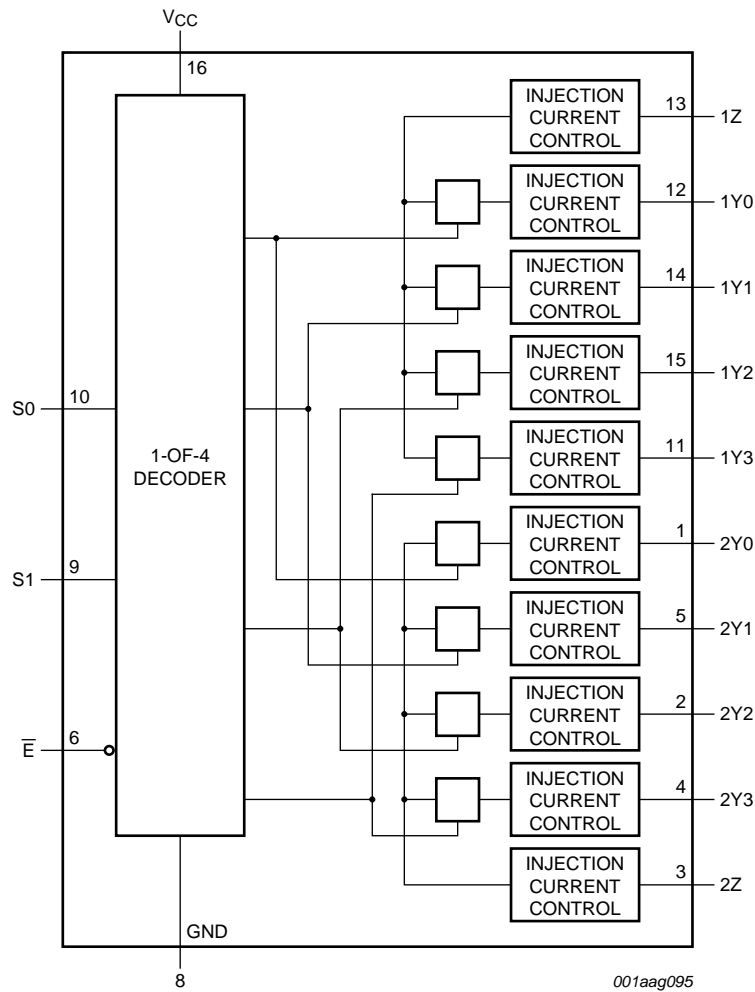


Fig 3. Functional diagram

6. Pinning information

6.1 Pinning

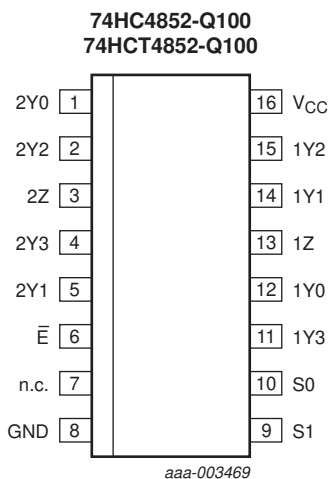
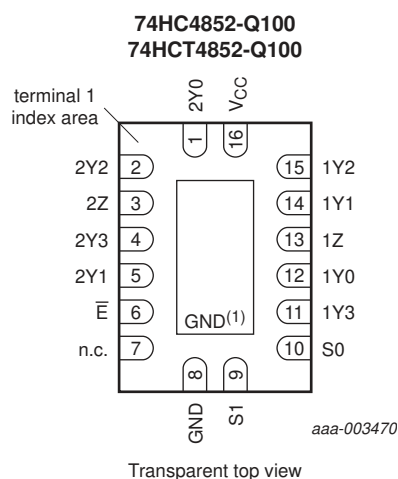


Fig 4. Pin configuration SO16 and TSSOP16



- (1) This is not a supply pin. The substrate is attached to this pad using conductive die attach material. There is no electrical or mechanical requirement to solder this pad. However, if it is soldered, the solder land should remain floating or be connected to GND.

Fig 5. Pin configuration DHVQFN16

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
2Y0	1	independent input/output
2Y2	2	independent input/output
2Z	3	common input/output
2Y3	4	independent input/output
2Y1	5	independent input/output
\bar{E}	6	enable input (active LOW)
n.c.	7	not connected
GND	8	ground (0 V)
S1	9	select input
S0	10	select input
1Y3	11	independent input/output
1Y0	12	independent input/output
1Z	13	common input/output
1Y1	14	independent input/output
1Y2	15	independent input/output
V _{CC}	16	supply voltage

7. Functional description

Table 3. Function table^[1]

Input			Channel ON
\bar{E}	S1	S0	
L	L	L	nY0 to nZ
L	L	H	nY1 to nZ
L	H	L	nY2 to nZ
L	H	H	nY3 to nZ
H	X	X	-

- [1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		^[1] -0.5	$V_{CC} + 0.5$	V
V_{SW}	switch voltage		^[2] -0.5	$V_{CC} + 0.5$	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	± 20	mA
I_{SK}	switch clamping current	$V_{SW} < -0.5$ V or $V_{SW} > V_{CC} + 0.5$ V	-	± 20	mA
I_{SW}	switch current	$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[3] -	500	mW

- [1] The minimum and maximum input voltage rating may be exceeded if the input clamping current rating is observed.
 [2] The minimum and maximum switch voltage rating may be exceeded if the switch clamping current rating is observed.
 [3] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For TSSOP16 package: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 For DHVQFN16 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	74HC4852-Q100			74HCT4852-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	-	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_{SW}	switch voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	6.0	1000	-	-	-	ns/V
		$V_{CC} = 3.0\text{ V}$	-	6.0	800	-	-	-	ns/V
		$V_{CC} = 3.3\text{ V}$	-	6.0	800	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	6.0	500	-	6.0	500	ns/V
		$V_{CC} = 6.0\text{ V}$	-	6.0	400	-	-	-	ns/V

10. Static characteristics

Table 6. R_{ON} resistance

At recommended operating conditions; voltages are referenced to GND (ground 0 V); For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC4852-Q100										
$R_{ON(peak)}$	ON resistance (peak)	$V_I = V_{CC}$ to GND; $\bar{E} = V_{IL}$								
		$V_{CC} = 2.0\text{ V}; I_{SW} = 2\text{ mA}$	-	400	650	-	670	-	700	Ω
		$V_{CC} = 3.0\text{ V}; I_{SW} \leq 2\text{ mA}$	-	215	330	-	360	-	380	Ω
		$V_{CC} = 3.3\text{ V}; I_{SW} \leq 2\text{ mA}$	-	120	270	-	305	-	345	Ω
		$V_{CC} = 4.5\text{ V}; I_{SW} \leq 2\text{ mA}$	-	76	210	-	240	-	270	Ω
		$V_{CC} = 6.0\text{ V}; I_{SW} \leq 2\text{ mA}$	-	59	195	-	220	-	250	Ω
ΔR_{ON}	ON resistance mismatch between channels	$V_I = 0.5 \times V_{CC}; \bar{E} = V_{IL}$								
		$V_{CC} = 2.0\text{ V}; I_{SW} = 2\text{ mA}$	-	4	10	-	15	-	20	Ω
		$V_{CC} = 3.0\text{ V}; I_{SW} \leq 2\text{ mA}$	-	2	8	-	12	-	16	Ω
		$V_{CC} = 3.3\text{ V}; I_{SW} \leq 2\text{ mA}$	-	2	8	-	12	-	16	Ω
		$V_{CC} = 4.5\text{ V}; I_{SW} \leq 2\text{ mA}$	-	2	8	-	12	-	16	Ω
		$V_{CC} = 6.0\text{ V}; I_{SW} \leq 2\text{ mA}$	-	3	9	-	13	-	18	Ω
74HCT4852-Q100										
$R_{ON(peak)}$	ON resistance (peak)	$V_I = V_{CC}$ to GND; $\bar{E} = V_{IL}$								
		$V_{CC} = 4.5\text{ V}; I_{SW} \leq 2\text{ mA}$	-	76	210	-	240	-	270	Ω
ΔR_{ON}	ON resistance mismatch between channels	$V_I = 0.5 \times V_{CC}; \bar{E} = V_{IL}$								
		$V_{CC} = 4.5\text{ V}; I_{SW} \leq 2\text{ mA}$	-	2	8	-	12	-	16	Ω

Table 7. Injection current coupling

At recommended operating conditions; voltages are referenced to GND (ground 0 V); For test circuit see [Figure 9](#).

Symbol	Parameter	Conditions	74HC4852/Q100			74HCT4852/Q100			Unit	
			Min	Typ ^[1]	Max	Min	Typ ^[1]	Max		
T_{amb} = -40 °C to +125 °C										
ΔV_O	output voltage variation	$ I_{SW} \leq 1 \text{ mA}; R_S \leq 3.9 \text{ k}\Omega$ ^{[2][3]}	$V_{CC} = 3.3 \text{ V}$	-	0.05	1	-	-	-	mV
			$V_{CC} = 5.0 \text{ V}$	-	0.03	1	-	0.03	1	mV
		$ I_{SW} \leq 10 \text{ mA}; R_S \leq 3.9 \text{ k}\Omega$	$V_{CC} = 3.3 \text{ V}$	-	0.55	5	-	-	-	mV
			$V_{CC} = 5.0 \text{ V}$	-	0.27	5	-	0.27	5	mV
		$ I_{SW} \leq 1 \text{ mA}; R_S \leq 20 \text{ k}\Omega$	$V_{CC} = 3.3 \text{ V}$	-	0.04	2	-	-	-	mV
			$V_{CC} = 5.0 \text{ V}$	-	0.03	2	-	0.03	2	mV
		$ I_{SW} \leq 10 \text{ mA}; R_S \leq 20 \text{ k}\Omega$	$V_{CC} = 3.3 \text{ V}$	-	0.56	20	-	-	-	mV
			$V_{CC} = 5.0 \text{ V}$	-	0.48	20	-	0.48	20	mV

[1] Typical values are measured at T_{amb} = 25 °C.

[2] ΔV_O here is the maximum variation of output voltage of an enabled analog channel when current is injected into any disabled channel.

[3] I_{SW} = total current injected into all disabled channels.

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC4852-Q100										
V _{IH}	HIGH-level input voltage	control inputs								
		$V_{CC} = 2.0 \text{ V}$	1.5	-	-	1.5	-	1.5	-	V
		$V_{CC} = 3.0 \text{ V}$	2.1	-	-	2.1	-	2.1	-	V
		$V_{CC} = 3.3 \text{ V}$	2.3	-	-	2.3	-	2.3	-	V
		$V_{CC} = 4.5 \text{ V}$	3.15	-	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 \text{ V}$	4.2	-	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	control inputs								
		$V_{CC} = 2.0 \text{ V}$	-	-	0.5	-	0.5	-	0.5	V
		$V_{CC} = 3.0 \text{ V}$	-	-	0.9	-	0.9	-	0.9	V
		$V_{CC} = 3.3 \text{ V}$	-	-	1.0	-	1.0	-	1.0	V
		$V_{CC} = 4.5 \text{ V}$	-	-	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	-	1.8	-	1.8	-	1.8	V
I _I	input leakage current	control inputs; V _I = GND or V _{CC}								
		$V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±0.1	-	±1.0	µA

Table 8. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I _{S(OFF)}	OFF-state leakage current	$\bar{E} = V_{IH}; V_I = \text{GND or } V_{CC}; V_O = V_{CC} \text{ or GND}; V_{CC} = 6.0 \text{ V};$ see Figure 6								
		nYn; per channel	-	-	±0.1	-	±0.5	-	±1.0	µA
		nZ; all channels	-	-	±0.2	-	±2.0	-	±4.0	µA
I _{S(ON)}	ON-state leakage current	$\bar{E} = V_{IL}; V_I = \text{GND or } V_{CC}; V_O = V_{CC} \text{ or GND}; V_{CC} = 6.0 \text{ V};$ see Figure 7	-	-	±0.1	-	±0.5	-	±1.0	µA
I _{CC}	supply current	$V_I = \text{GND or } V_{CC}$ $V_{CC} = 6.0 \text{ V}$	-	-	2.0	-	5.0	-	20.0	µA
C _I	input capacitance	S0, S1, S2 and \bar{E}	-	2	10	-	10	-	10	pF
C _{SW}	switch capacitance	nZ; OFF-state	-	15	40	-	40	-	40	pF
		nYn; OFF-state	-	3	15	-	15	-	15	pF
74HCT4852-Q100										
V _{IH}	HIGH-level input voltage	control inputs								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	control inputs								
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	0.8	-	0.8	-	0.8	V
I _I	input leakage current	control inputs; $V_I = \text{GND or } V_{CC}$ $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±0.1	-	±1.0	µA
I _{S(OFF)}	OFF-state leakage current	$\bar{E} = V_{IH}; V_I = \text{GND or } V_{CC}; V_O = V_{CC} \text{ or GND}; V_{CC} = 5.5 \text{ V};$ see Figure 6								
		per channel	-	-	±0.1	-	±0.5	-	±1.0	µA
		all channels	-	-	±0.2	-	±2.0	-	±4.0	µA
I _{S(ON)}	ON-state leakage current	$\bar{E} = V_{IL}; V_I = \text{GND or } V_{CC}; V_O = V_{CC} \text{ or GND}; V_{CC} = 5.5 \text{ V};$ see Figure 7	-	-	±0.1	-	±0.5	-	±1.0	µA
I _{CC}	supply current	$V_I = \text{GND or } V_{CC}$ $V_{CC} = 5.5 \text{ V}$	-	-	2.0	-	5.0	-	20.0	µA
ΔI _{CC}	additional supply current	control inputs; $V_I = V_{CC} - 2.1 \text{ V};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}; I_O = 0 \text{ A}$	-	-	300	-	370	-	370	µA
C _I	input capacitance	S0, S1, S2 and \bar{E}	-	2	10	-	10	-	10	pF
C _{SW}	switch capacitance	nZ; OFF-state	-	9	40	-	40	-	40	pF
		nYn; OFF-state	-	3	15	-	15	-	15	pF

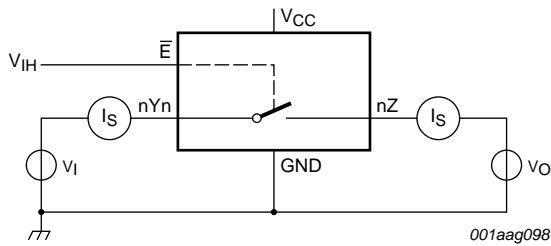


Fig 6. Test circuit for measuring OFF-state leakage current

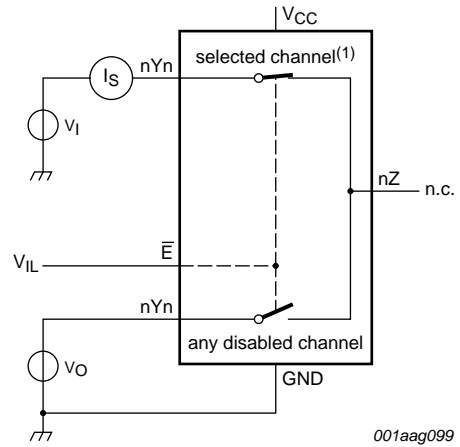
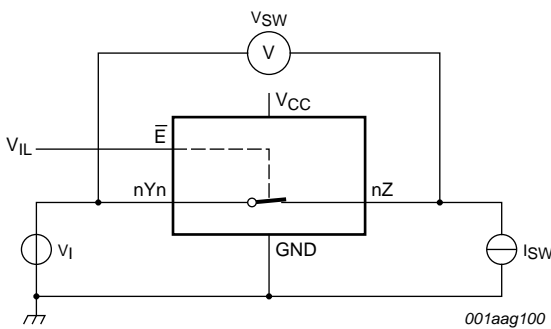


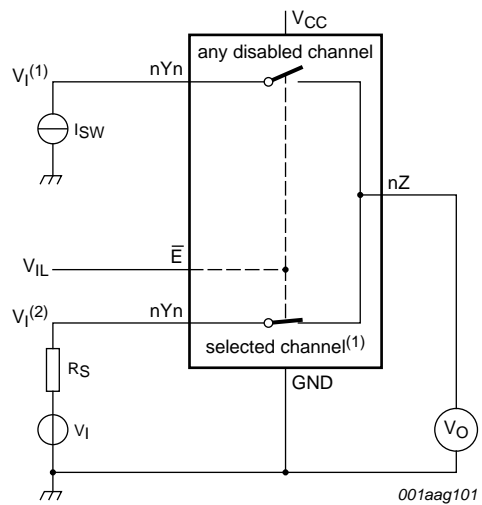
Fig 7. Test circuit for measuring ON-state leakage current

(1) Channel is selected by S0 and S1.



$$R_{ON} = V_{SW} / I_{SW}$$

Fig 8. Test circuit for measuring ON resistance



(1) Channel is selected by S0 and S1.

$V_i^{(1)} < GND$ or $V_i^{(1)} > V_{CC}$.

$GND < V_i^{(2)} < V_{CC}$.

Fig 9. Test circuit for injection current coupling

11. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for load circuit see [Figure 14](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit	
			Min	Typ	Max	Min	Max	Min	Max		
74HC4852-Q100											
t_{pd}	propagation delay	nZ, nYn to nYn, nZ; see Figure 10 [1]									
		$V_{CC} = 2.0\text{ V}$	2.2	9.3	33	2.2	34	2.2	35	ns	
		$V_{CC} = 3.0\text{ V}$	2.2	4.9	16.5	1.9	18	1.9	19.5	ns	
		$V_{CC} = 3.3\text{ V}$	2.0	4.4	15.0	1.6	16.5	1.6	18.5	ns	
		$V_{CC} = 4.5\text{ V}$	1.6	3.2	11.6	1.1	12.5	1.1	13.5	ns	
		$V_{CC} = 6.0\text{ V}$	1.5	2.5	10.2	0.9	11	0.9	12	ns	
		Sn to nZ, nYn; see Figure 11 [1]									
		$V_{CC} = 2.0\text{ V}$	7.7	16.8	38	6.3	40	6.3	42	ns	
		$V_{CC} = 3.0\text{ V}$	4.9	8.8	20	3.9	21.5	3.9	23	ns	
		$V_{CC} = 3.3\text{ V}$	4.4	7.9	17.5	3.4	19	3.4	22	ns	
		$V_{CC} = 4.5\text{ V}$	3.2	5.8	14	2.3	15	2.3	17	ns	
$V_{CC} = 6.0\text{ V}$	2.4	4.8	12.6	1.6	14.5	1.6	16.5	ns			
t_{en}	enable time	\bar{E} to nZ, nYn; see Figure 12 [2]									
		$V_{CC} = 2.0\text{ V}$	10.5	20.5	47.5	8.5	52.5	8.5	57.5	ns	
		$V_{CC} = 3.0\text{ V}$	6.2	10.6	45	5.2	50	5.2	55	ns	
		$V_{CC} = 3.3\text{ V}$	5.6	9.4	42.5	4.6	47.5	4.6	52.5	ns	
		$V_{CC} = 4.5\text{ V}$	4.2	6.9	40	3	45	3	50	ns	
		$V_{CC} = 6.0\text{ V}$	3.2	5.6	39	2.2	40	2.2	40	ns	
t_{dis}	disable time	\bar{E} to nZ, nYn; see Figure 12 [3]									
		$V_{CC} = 2.0\text{ V}$	39.5	75.4	100	39.3	105	39	115	ns	
		$V_{CC} = 3.0\text{ V}$	35.2	69.5	90	35.5	100	35	110	ns	
		$V_{CC} = 3.3\text{ V}$	34.6	68.1	85	34.6	95	34.5	105	ns	
		$V_{CC} = 4.5\text{ V}$	28.5	63	80	28.2	90	28	100	ns	
		$V_{CC} = 6.0\text{ V}$	14.4	57.9	78	13.5	80	13.0	80	ns	
C_{PD}	power dissipation capacitance	per channel; see Figure 13 [4]									
		$V_{CC} = 3.3\text{ V}$	-	42	-	-	-	-	-	pF	
		$V_{CC} = 5.0\text{ V}$	-	47	-	-	-	-	-	pF	

Table 9. Dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground 0 V); for load circuit see [Figure 14](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT4852-Q100										
t _{pd}	propagation delay	nZ, nYn to nYn, nZ; see Figure 10 [1]								
		V _{CC} = 4.5 V	1.6	3.5	11.5	1.1	12.5	1.1	13.5	ns
		Sn to nZ, nYn; see Figure 11 [1]								
		V _{CC} = 4.5 V	3.2	7.6	13	2.3	15	1.6	17	ns
t _{en}	enable time	\bar{E} to nZ, nYn; see Figure 12 [2]								
		V _{CC} = 4.5 V	4.2	8.3	25	3.0	30	3.0	35	ns
t _{dis}	disable time	\bar{E} to nZ, nYn; see Figure 12 [3]								
		V _{CC} = 4.5 V	28.5	61.8	80	28.2	90	28.0	100	ns
C _{PD}	power dissipation capacitance	per channel; see Figure 13 [4]								
		V _{CC} = 5.0 V	-	47	-	-	-	-	-	pF

- [1] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [2] t_{en} is the same as t_{PZH} and t_{PZL}.
- [3] t_{dis} is the same as t_{PLZ} and t_{PHZ}.
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum\{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\}$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 $\sum\{(C_L + C_{sw}) \times V_{CC}^2 \times f_o\}$ = sum of outputs;
 C_L = output load capacitance in pF;
 C_{sw} = switch capacitance in pF;
 V_{CC} = supply voltage in V.

12. Waveforms

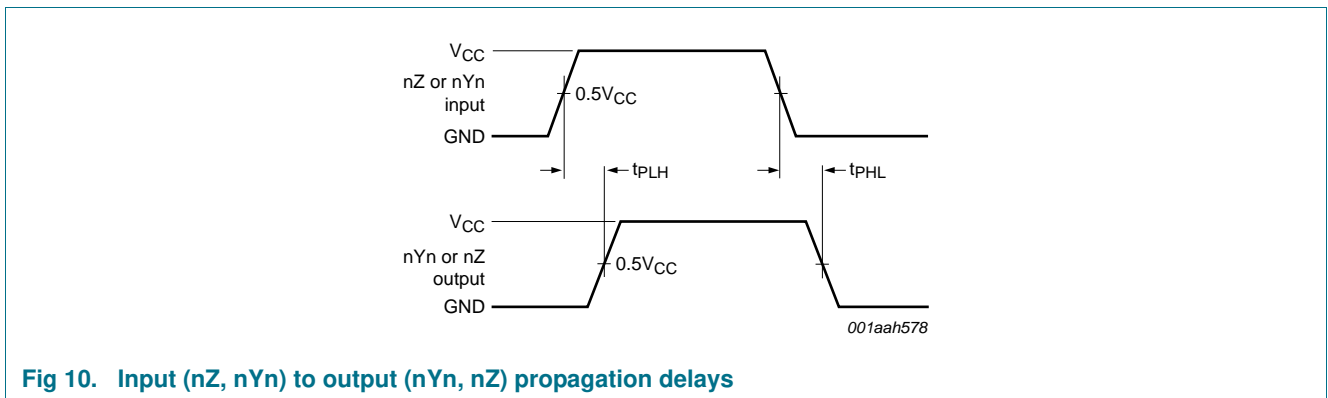
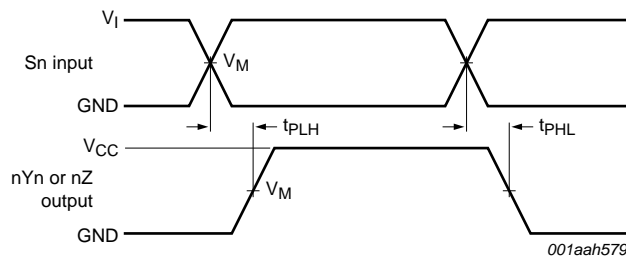
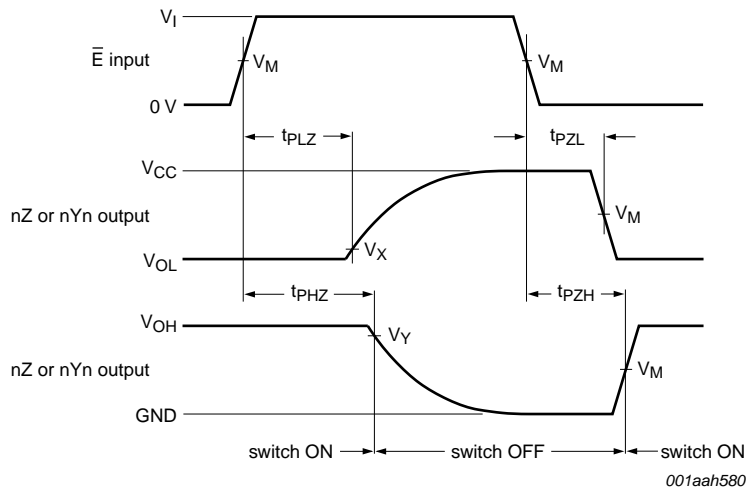


Fig 10. Input (nZ, nYn) to output (nYn, nZ) propagation delays



Measurement points are given in [Table 10](#).

Fig 11. Input (Sn) to output (nYn, nZ) propagation delays



Measurement points are shown in [Table 10](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 12. Enable and disable times

Table 10. Measurement points

Type	Input		Output		
	V_M	V_I	V_M	V_X	V_Y
74HC4852-Q100	$0.5V_{CC}$	V_{CC}	$0.5V_{CC}$	$V_{OL} + 0.1(V_{CC} - V_{OL})$	$0.9V_{OH}$
74HCT4852-Q100	1.3 V	3.0 V	$0.5V_{CC}$	$V_{OL} + 0.1(V_{CC} - V_{OL})$	$0.9V_{OH}$

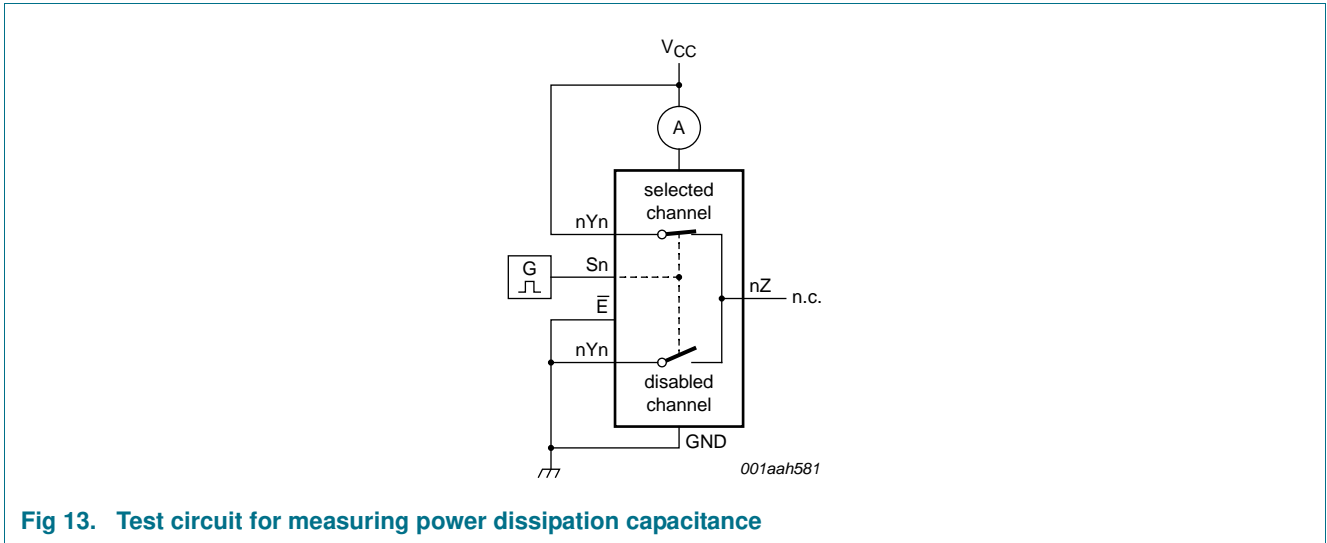
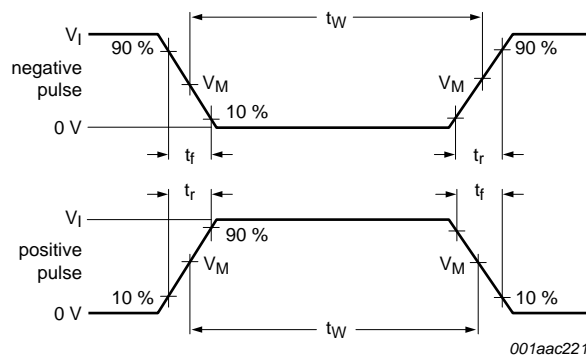
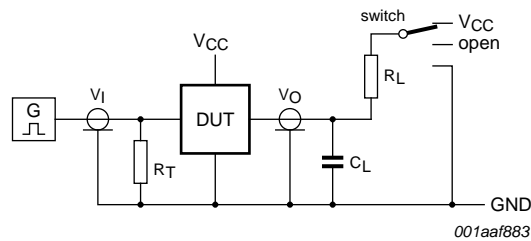


Fig 13. Test circuit for measuring power dissipation capacitance



a. Input pulse definition



Definitions for test circuit:

R_L = load resistance.

C_L = load capacitance including jig and probe capacitance.

R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator.

b. Load circuit

Test data is given in [Table 11](#).

Fig 14. Input pulse definition and load circuit

Table 11. Test data

Test	Input			Output		S1 position
	Control \bar{E} , Sn	Switch nYn (nZ)	t_r, t_f	Switch nZ (nYn)		
	V_I ^[1]	V_I		C_L	R_L	
t_{PHL}, t_{PLH}	V_{CC}	V_{CC}	6 ns	50 pF	-	open
t_{PHZ}, t_{PZH}	V_{CC}	V_{CC}	6 ns	50 pF	10 k Ω	GND
t_{PLZ}, t_{PZL}	V_{CC}	V_{CC}	6 ns	50 pF	10 k Ω	V_{CC}
C_{PD}	V_{CC}	V_{CC}	6 ns	0 pF	-	open

[1] For 74HCT4852-Q100: input voltage $V_I = 3.0$ V.

13. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

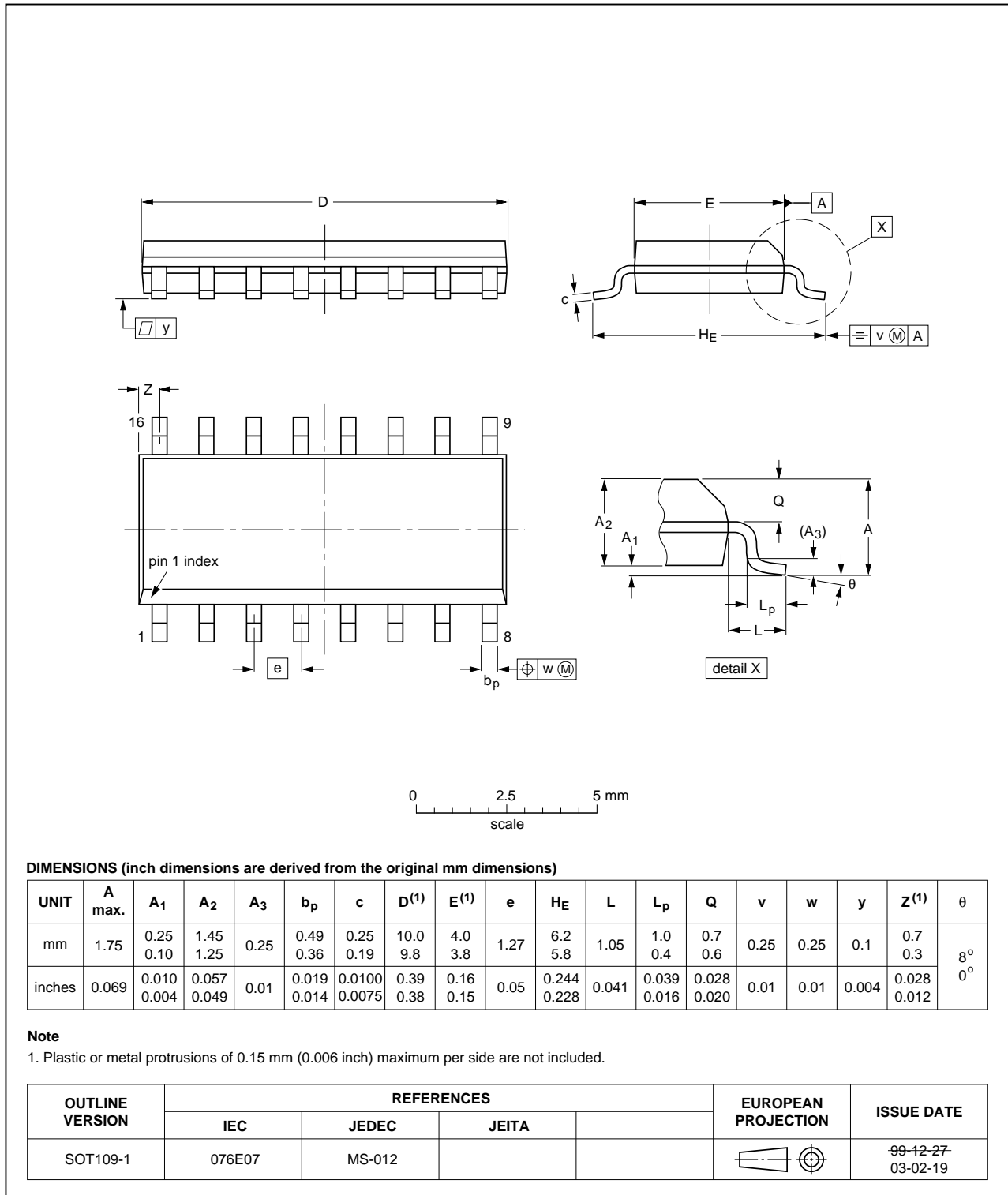


Fig 15. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

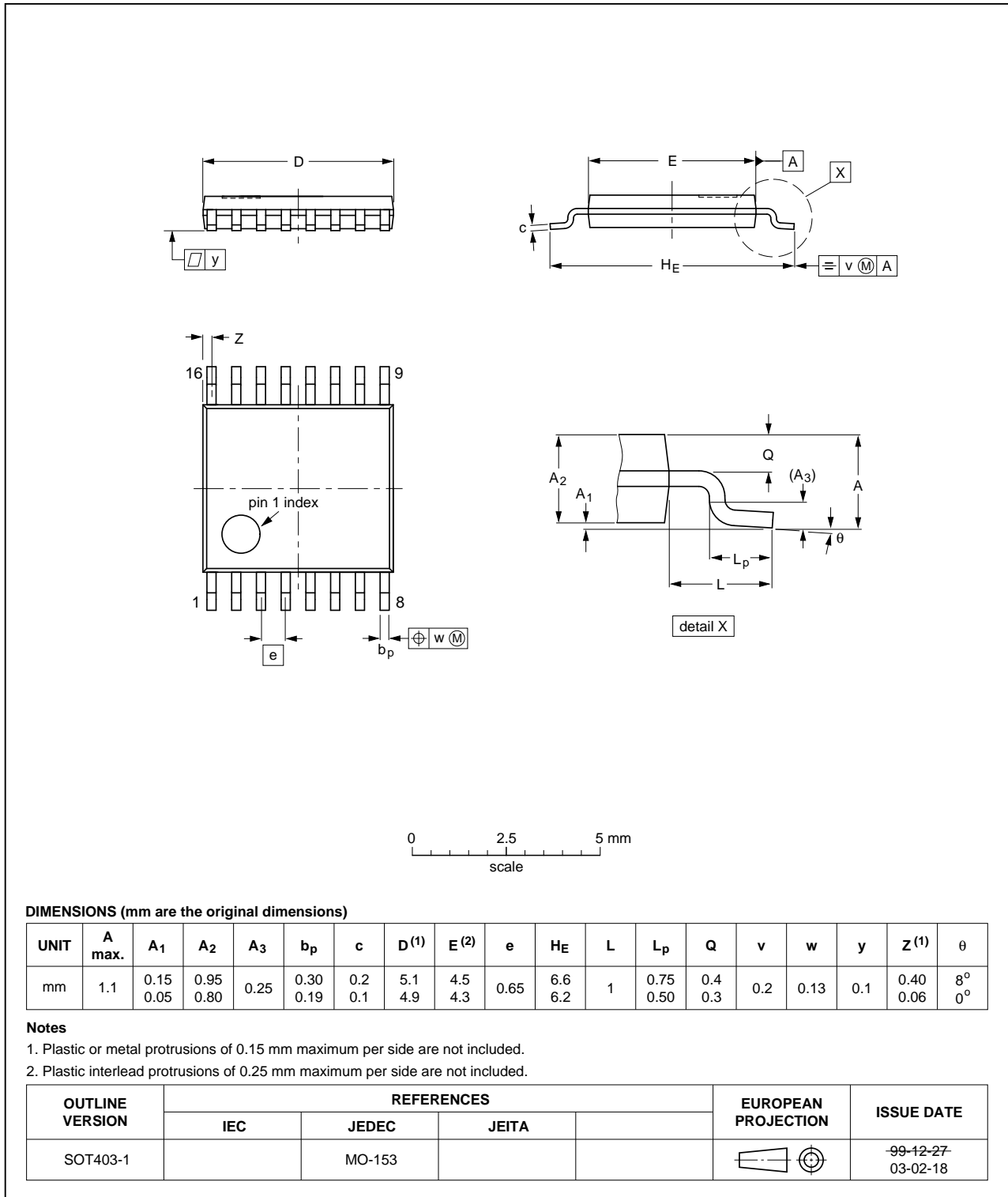


Fig 16. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1

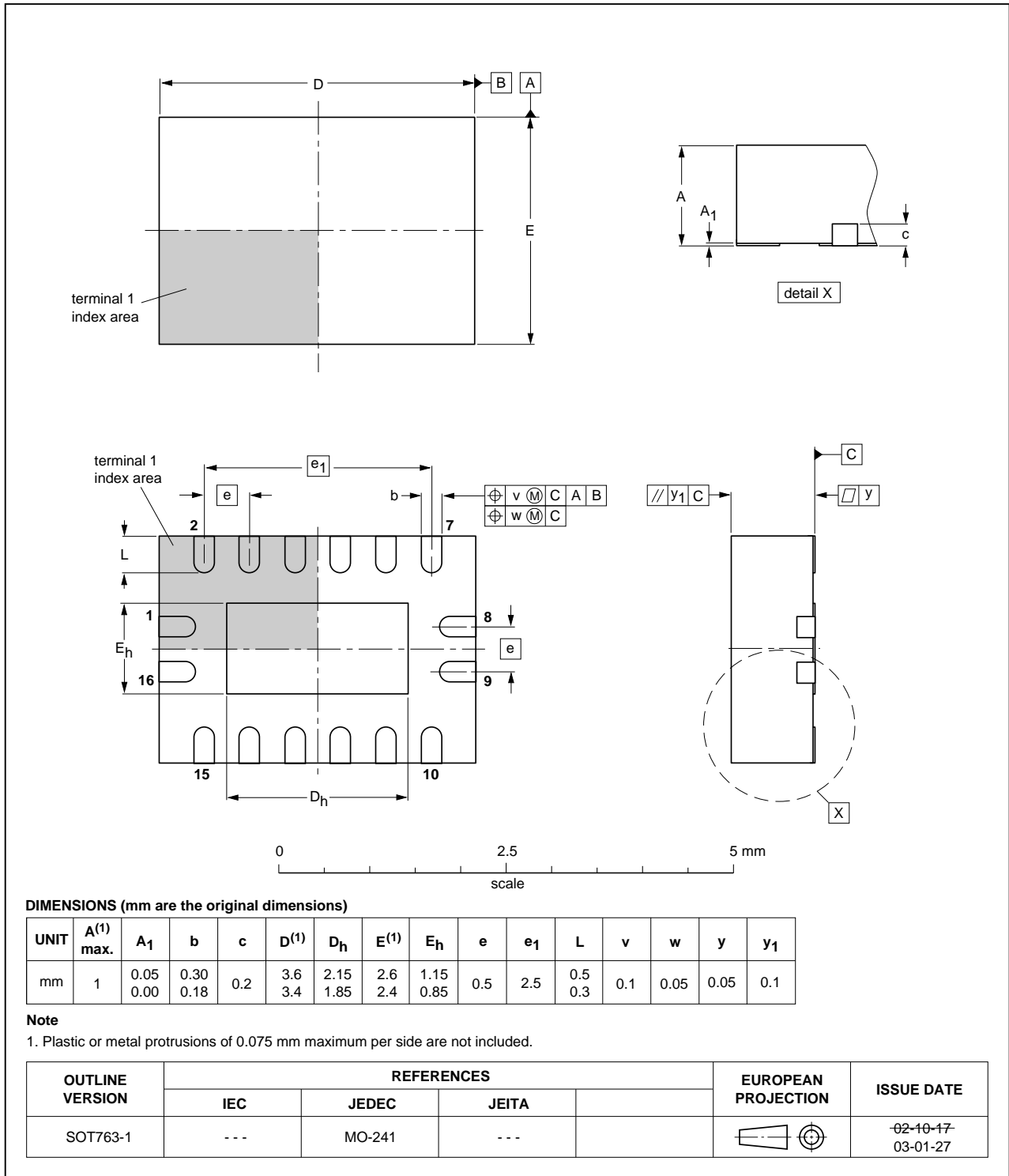


Fig 17. Package outline SOT763-1 (DHVQFN16)

14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4852_Q100_1	20120712	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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